



Effects of FIB Processing on Local Measurements of Solar Cells

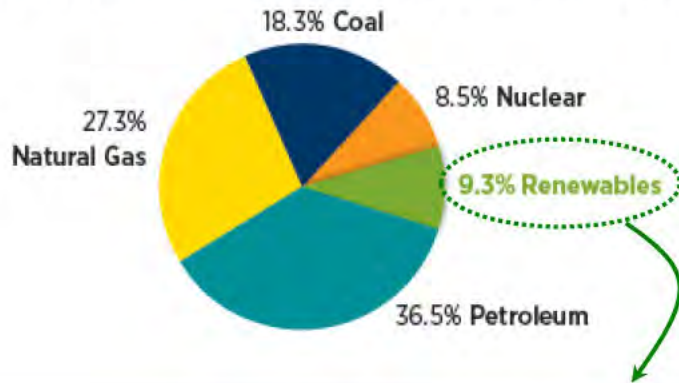
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(February 27, 2014)

Energy consumption, and renewable capacity

U.S. Energy Consumption (2012): 95.1 Quadrillion Btu^{*1}



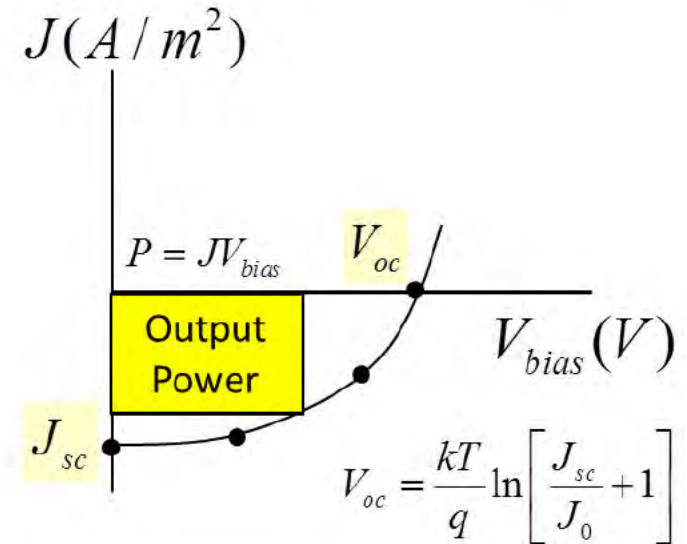
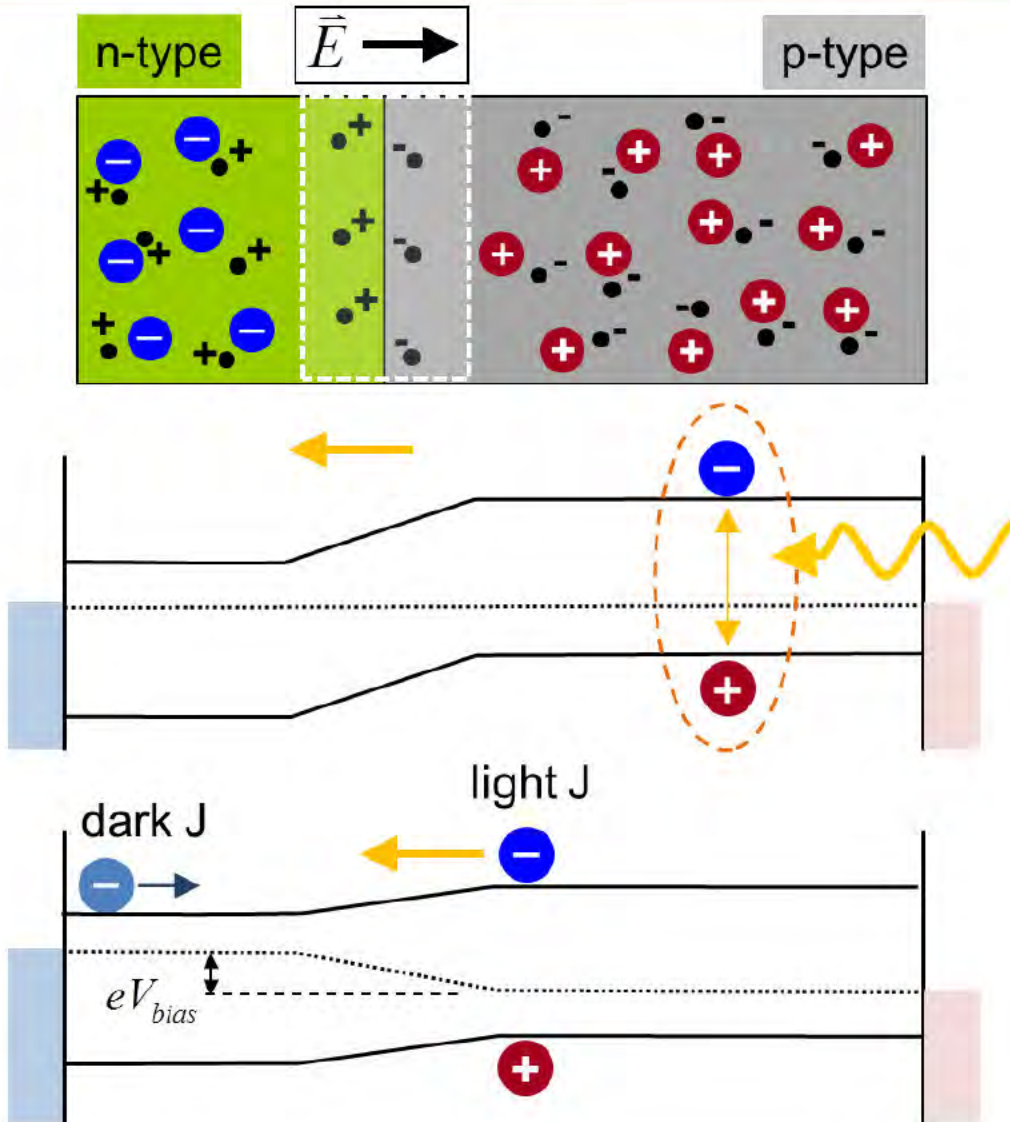
[Q] Size of PV area to cover all US energy consumption?

- US Energy consumption rate^{*2} = 3×10^{12} W
- Time-averaged solar energy flux = 250 W/m^2
- Best conversion efficiency = 33%

→ Pure PV area of (150 miles)²

^{*2} <http://www.eia.gov/forecasts/ieo/index.cfm>

Extracting photo-carriers with p-n junction



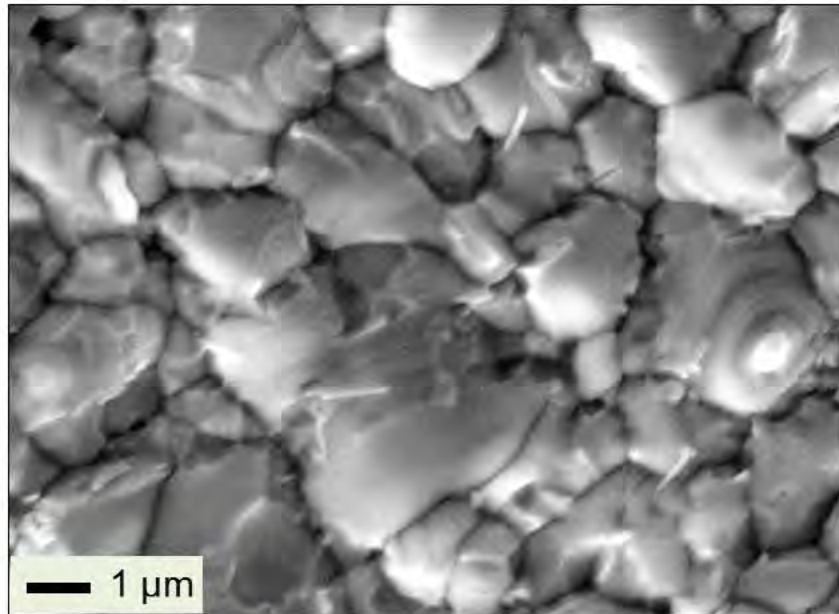
$$\eta = \frac{P_{out}}{P_{in}} = \frac{J_{sc} \times V_{oc} \times F.F.}{P_{in}}$$

η : power conversion efficiency

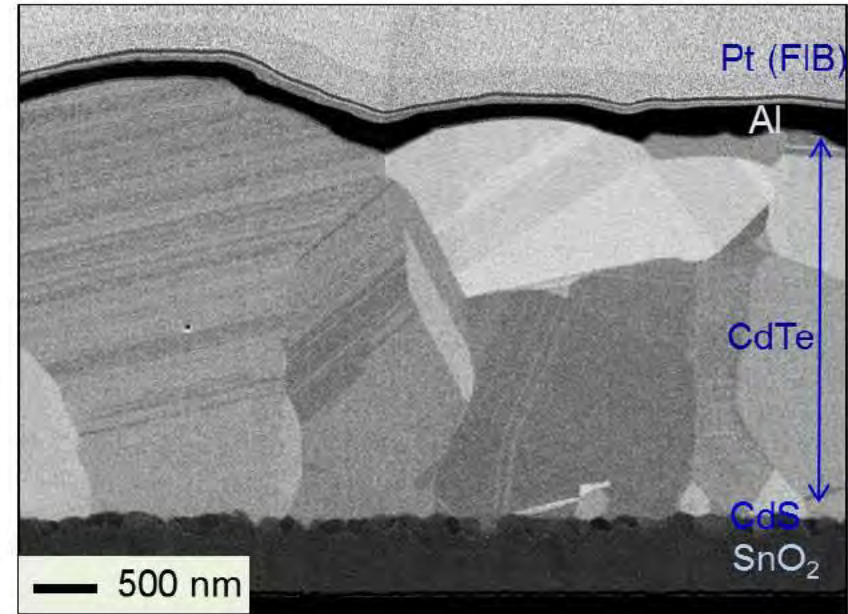
- J_{sc} : short-circuit current
- J_0 : dark current
- V_{oc} : open-circuit voltage
- FF : fill factor

Microstructure of thin-film PV: highly defective

top view



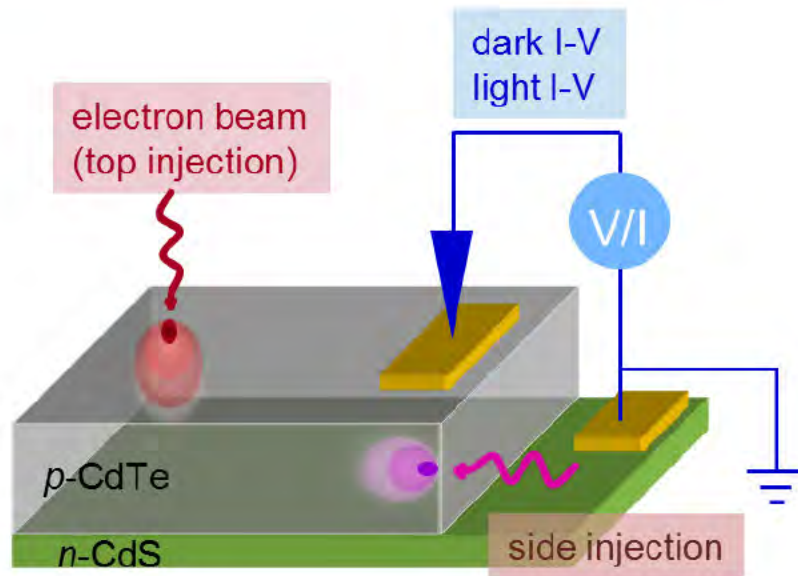
cross section



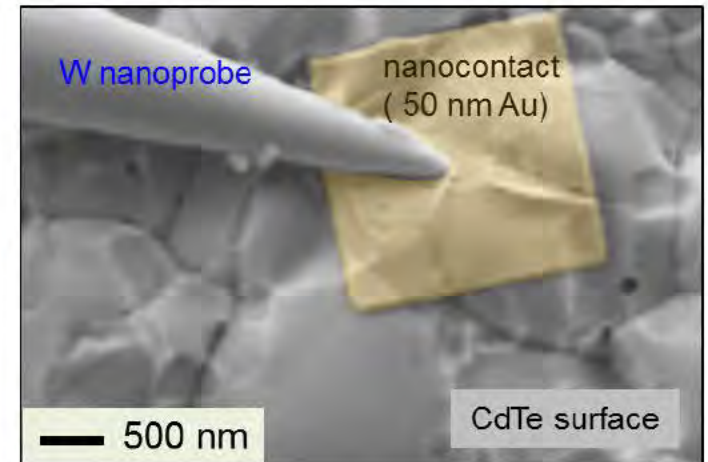
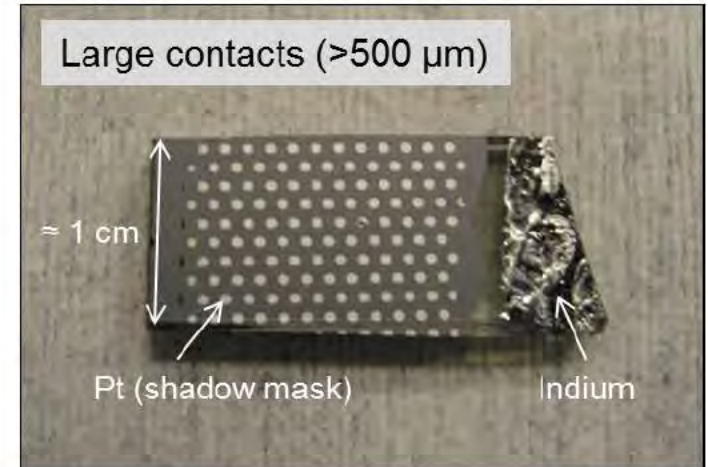
- Comprised of grains (100's nm ~ a few μm): lots of grain boundaries (GBs)
- Local variation of chemical composition / defects
- **impact of grain boundaries on efficiency: mainly unknown**

Need for metrology to access properties of individual GB / GI (grain interior)

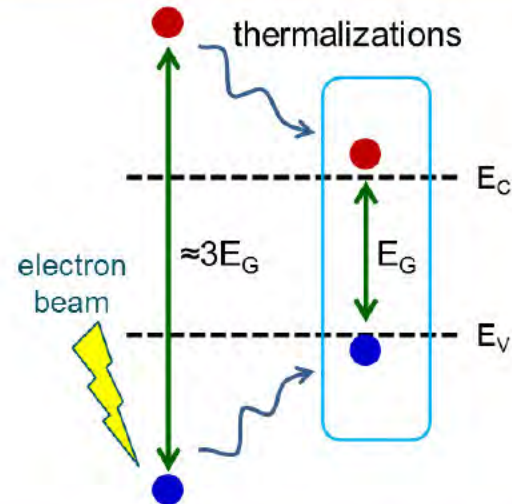
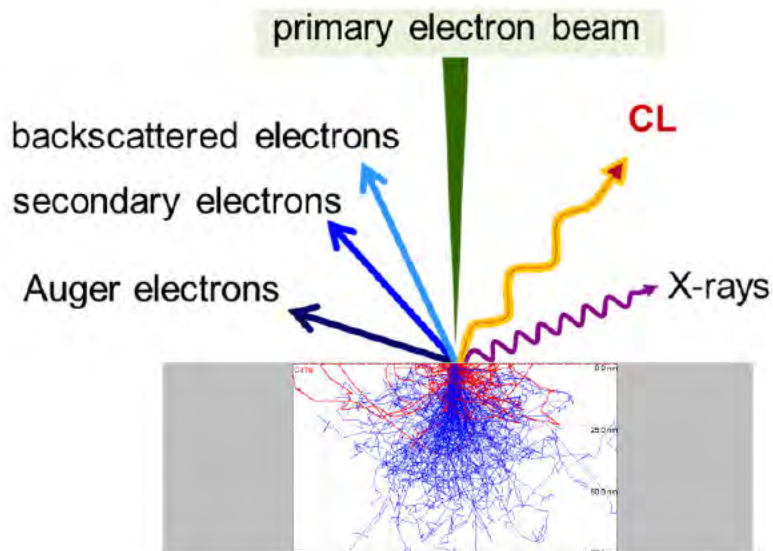
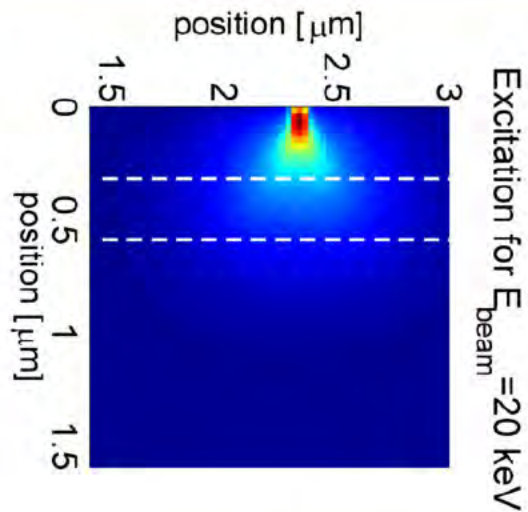
Electron Beam Induced Current (EBIC)



- Local carrier generation with a point injection ($(110 \text{ nm})^3$ at 5 kV, $(1.5 \text{ }\mu\text{m})^3$ at 20 kV in CdTe)
- Beam injection: top surface, cross-section
- Nano-contacts at GBs / GIs
- Probe local PV properties of individual grain / grain boundary



Electron beam generates electron-hole pairs.



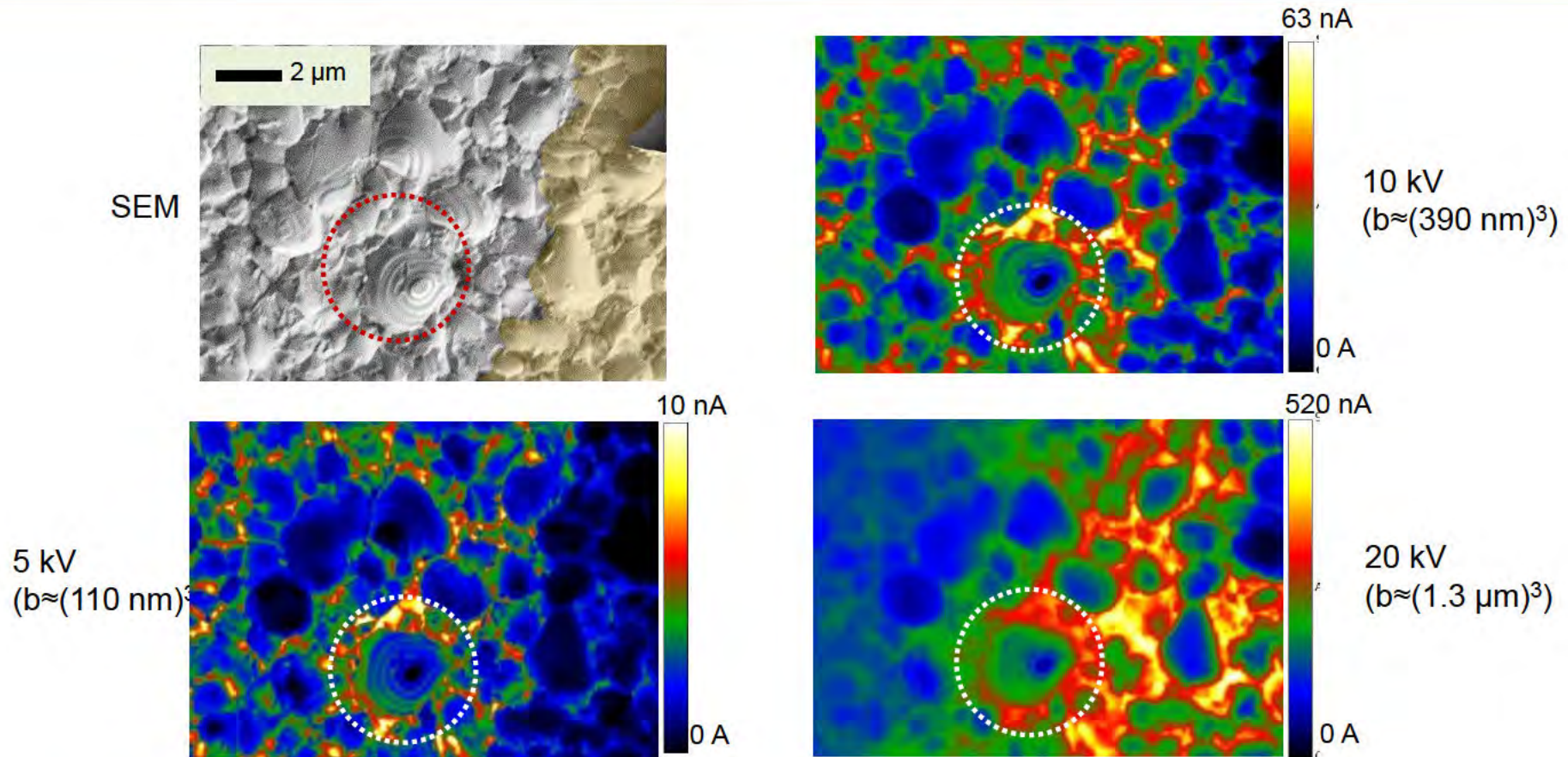
$$(\# \text{ of EHPs}) \approx \frac{(\text{deposited e - beam energy})}{3 \times (\text{energy band - gap})}$$

e.g. CdTe: $E_G = 1.5 \text{ eV}$, $E_b = 10 \text{ keV}$ (BSE $\approx 30 \%$)

$\Rightarrow \approx 1600 \text{ ehp}$

$$(\text{EBIC efficiency}) = \frac{(\text{measured EBIC})}{(\text{beam current})(\# \text{ of EHPs})}$$

Low keV, high-resolution EBIC

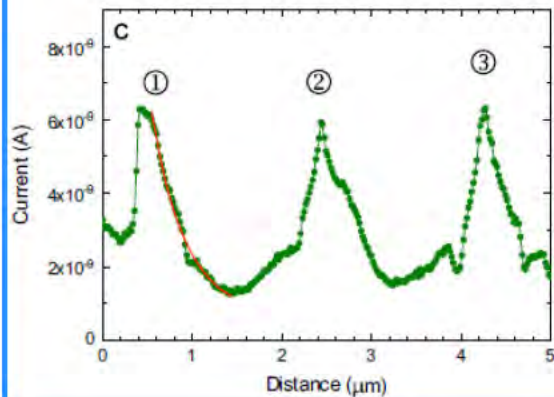
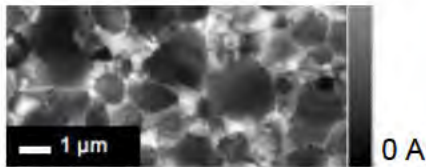


- Current increases as e-h bulb size increases.
- Higher collection at GBs
- Passivated GBs confine and direct carriers (\downarrow recombination, \uparrow IQE).

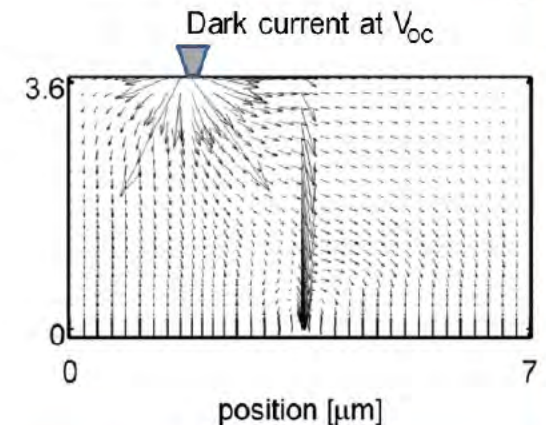
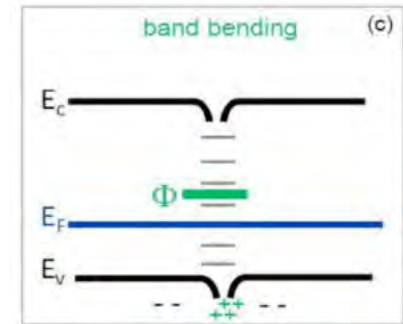
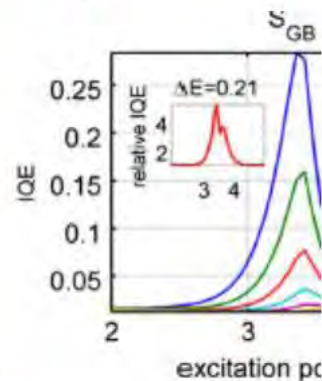
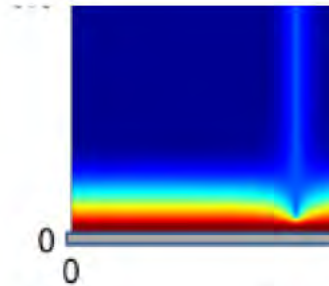
Modeling explains high carrier collection at GB.

Experiment (3 keV EBIC)

11 nA



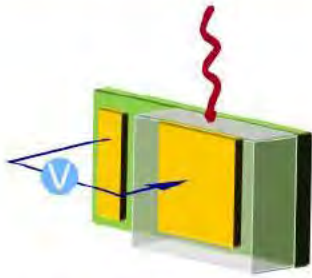
Modeling



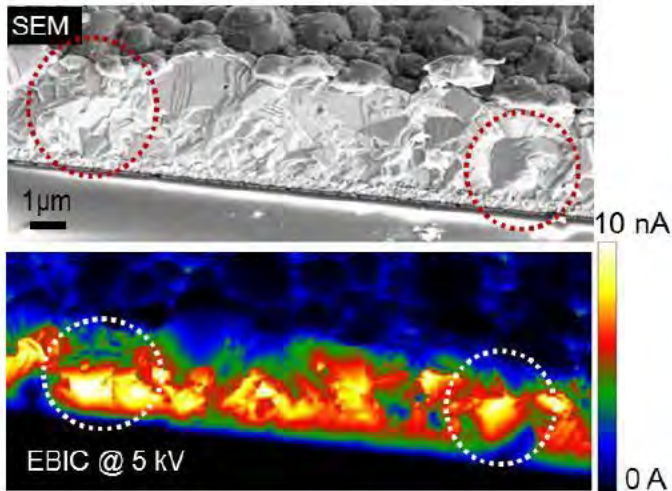
- GBs enhance photo-carrier collection properties (due to the band-bending).
- Model shows high leakage current at V_{OC} near GBs.

→ Overall impact of GBs: good for low quality PV vs. bad for high quality PV

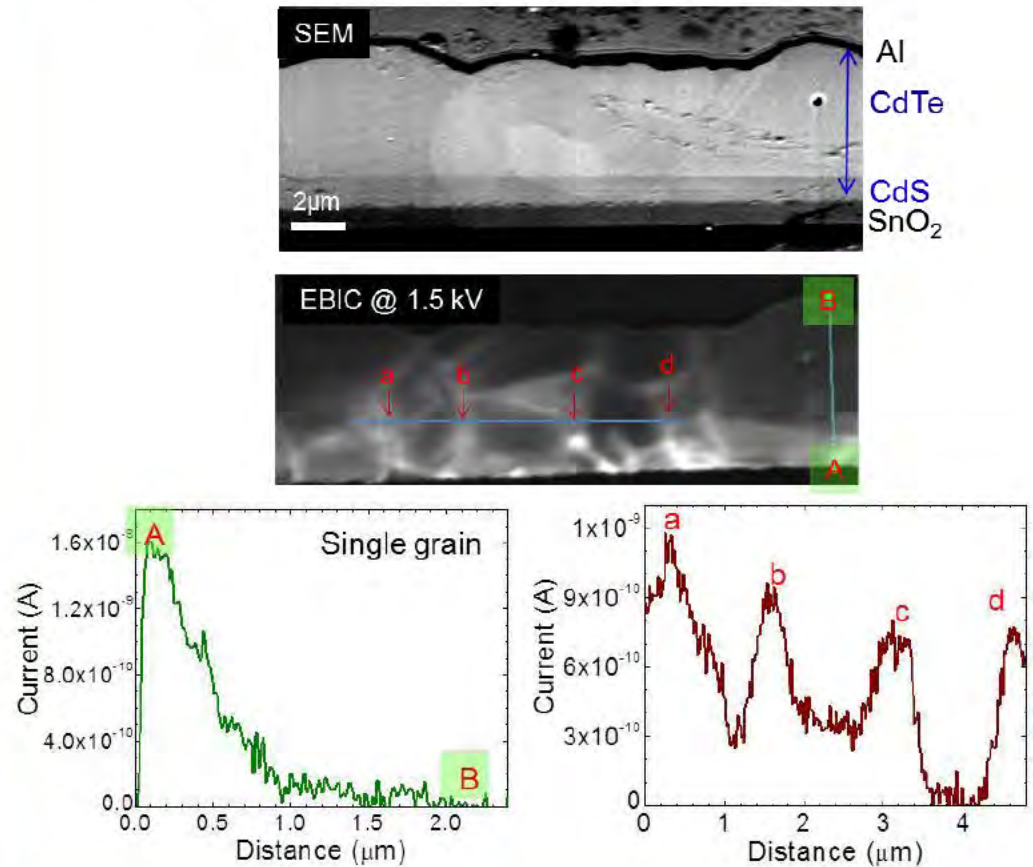
FIB processing creates smooth surface.



(1) Cleaved device



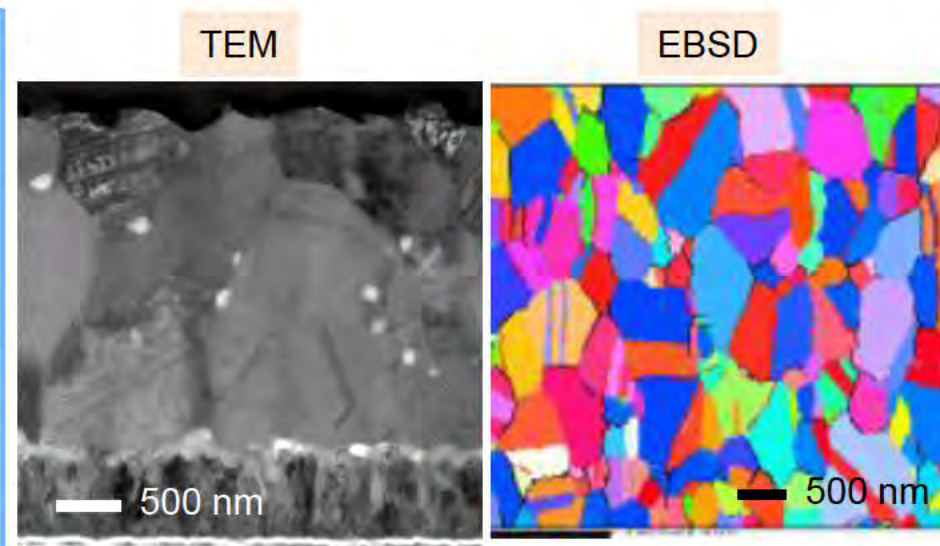
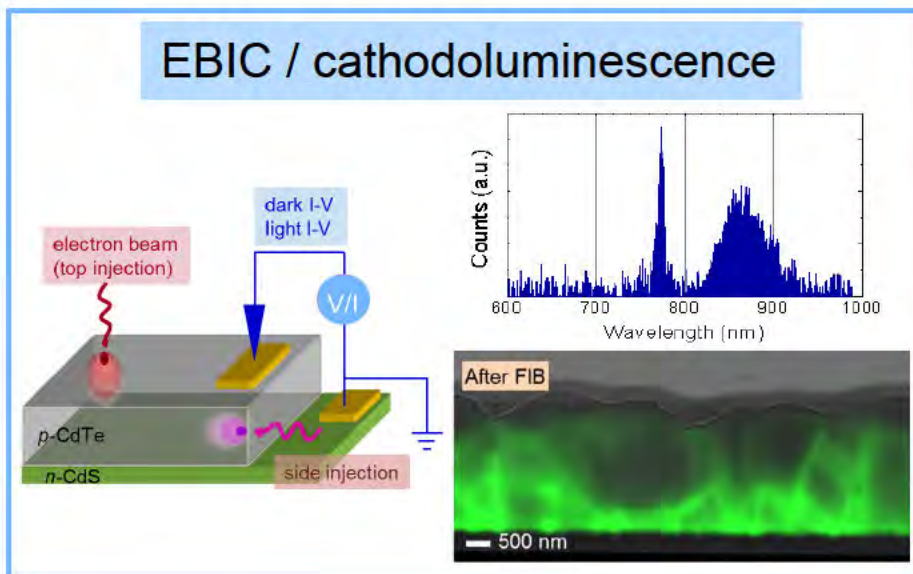
(2) FIB processed device



- Higher current at GBs
- GB efficiently serve as 3D contacts collecting minority carriers

Summary

- ✓ Physics of photovoltaic is important and exciting.
- ✓ **Low-energy, high-resolution EBIC** would be very informative technique for photovoltaic devices.
- ✓ Combination of local detection and local injection for sub-surface microscopy (10 nm to 200 nm scale)
→ electrical, optical, chemical, structural properties



Acknowledgement



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(TEM)

Research participants / collaborators

- CdTe solar cell (U. Toledo, GE/First Solar)
- CIGS solar cell (U. Toledo, NRL)
- CZTS solar cell (DuPont)
- Si solar cells: epi Si, high-efficiency PV (NREL)
- Perovskites (U. Nebraska)
- Organic PV

Thank you for your attention!